P Channel MOSFET

multicomp PRO

RoHS Compliant



Features

- VDS (V) =-30V
- ID =-7.5A
- Rds(on) < 30mΩ (Vgs =-10V)
- $R_{DS(ON)} < 45m\Omega (V_{GS} = -4.5V)$

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		Vds	-30	v	
Gate-Source Voltage		Vgs	±20	V	
Continuous Drain Current	(Note 1a)	lo	-7.5		
Pulsed Drain Current		Ідм	-20	A	
Continuous Drain-Source Diode Forward Current		ls	-2.5]	
Maximum Power Dissipation	(Note 1a)	PD	3		
	(Note 1b)		1.3	W	
	(Note 1c)		1.1	1	
Thermal Resistance, Junction- to-Ambient	(Note 1a)	Reja	42	°C/W	
Thermal Resistance, Junction- to-Case	(Note 1)	Rejc	12		
Operating and Storage Temperature Range		TJ, TSTG	-65 to + 150	°C	

Note 1: R⁰JA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R⁰JC is guaranteed by design while R⁰CA is defined by users. For general reference: Applications on 4.5" × 5" FR-4 PCB under still air environment. typical R⁰JA is found to be:

a. 42°C/W when mounted on a 1 in² pad of 2oz copper.

b. 95°C/W when mounted on a 0.066in² pad of 2oz copper.

c. 110°C/W when mounted on a 0.00123in² pad of 2oz copper.

Electrical Characteristics (TA = 25°C unless otherwise noted)

Characteristic	Symbol	Conditions		Тур	Max	Unit
Off Characteristics	í î					
Drain-to-Source Breakdown Voltage	VDSS	I ⊳=250µA, V Gs=0V	-30			V
Zero Gate Voltage Drain Current		VDS=-24V, VGS=0V			-1	μA
	IDSS	VDs=-24V, VGs=0V, TJ = 55°C			-10	
Gate-Body Leakage Current	Igss)	VDS=0V, VGS=±20V			±100	nA
On Characteristics (Note 1)						
Gate Threshold Voltage	VGS(th)	Vds=Vgs Id=-250µA	-1	-1.5	-3	V

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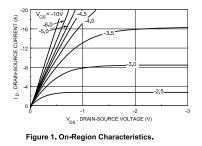
Characteristic	Symbol	Conditions	Min	Тур	Мах	Unit
Static Drain-Source On-Resistance		Vgs=-10V, Id=-7.5A	30		30	1
	RDS(On)	Vgs=-10V, Ib=-7.5A, TJ = 125°C			54	mΩ
		Vgs=-4.5V, Id=-6A			45	
On-State Drain Current		Vgs = -10 V , Vds = - 5 V	-20			A
	D(on)	Vgs = -4.5 V, Vds = - 5 V	-10			
Forward Transconductance	g FS	Vds=-10V, Id=-7.5A		13		S
Dynamic Characteristics (Note 2)	n					
Input Capacitance	Ciss	Vos=-15V, Vos=0V, f=1MHz		1440		pF
Output Capacitance	Coss			905		
Reverse Transfer Capacitance	Crss			355		
Switching Characteristics (Note 2)						
Turn-On DelayTime	td(on)	Vdd = -15 V, Id = -7 A, Vgen = -10 V, Rgen = 12Ω		10	20	nS
Turn-On Rise Time	tr			65	120	
Turn-Off DelayTime	td(off)			70	130	
Turn-Off Fall Time	tr				130	
Total Gate Charge	Qg	V _{DS} = -10 V, I _D = -7.5 A, V _{GS} = -10 V		47	67	nC
Gate Source Charge	Qgs			5		
Gate Drain Charge	Qgd	VG310 V		12		
Drain-Source Diode Characteristics			n			
Diode Forward Voltage (Note 2)	Vsd	Isd=-2.5A, Vgs=0V			-1.2	V
Reverse Recovery Time	trr	Vgs=0V, IF=-2.5 A, dIF/dt=100 A/µs			100	nS

NOTES:

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

2. Guaranteed by design, not subject to production

Typical Characterisitics



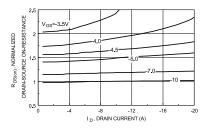
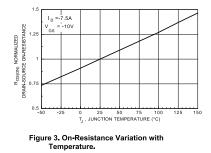


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.



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REVERSE DRAIN CURRENT (A)

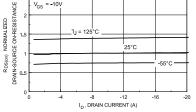


Figure 4. On Resistance Variation with Drain Current and Temperature.

125

PERATURE (°C)

- 250µ I_{D}

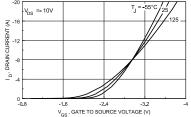
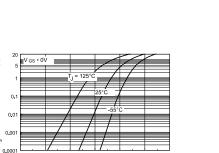


Figure 5. Transfer Characteristics.



ARD VOLTAGE (V

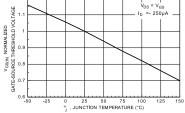


Figure 6. Gate Threshold Variation with Temperature.

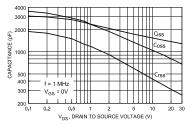
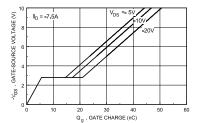


Figure 9. Capacitance Characteristics.



, JUNCTION TEMI

Figure 7. Breakdown Voltage Variation with Temperature.

Figure 10. Gate Charge Characteristics.

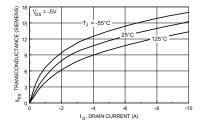
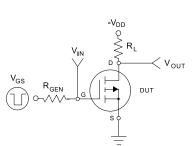


Figure 13. Transconductance Variation with Drain Current and Temperature.



BODY DIODE

Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

Figure 11. Switching Test Circuit.

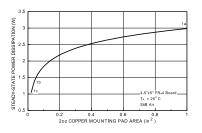


Figure 14. SOT-223 Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area

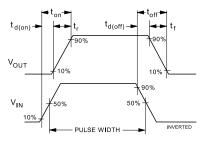


Figure 12. Switching Waveforms.

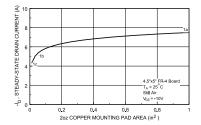


Figure 15. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.

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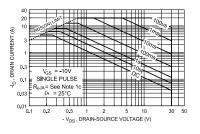


Figure 16. Maximum Safe Operating Area.

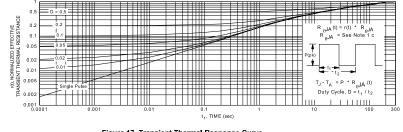
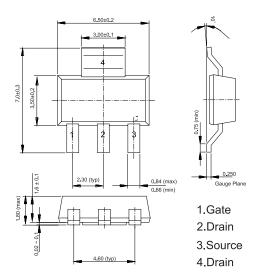
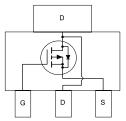


Figure 17. Transient Thermal Response Curve. Note: Thermal characterization performed using the conditions described in note 1c. Transient therm response will change depending on the circuit board design.

Diagram





Part Number Table

	Description	Part Number	
s : Millimetres	P Channel MOSFET, 5A, -7.5V, -30V	NDT452AP	

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